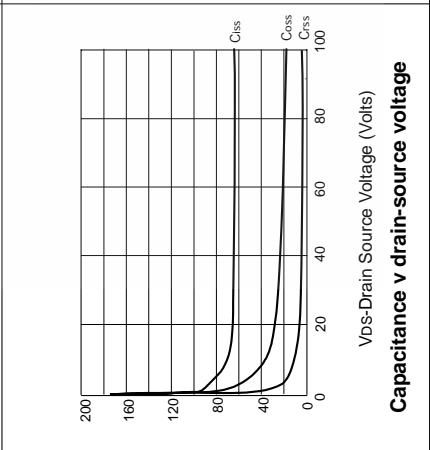
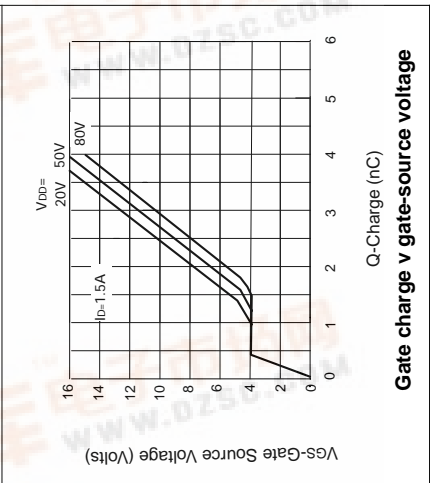
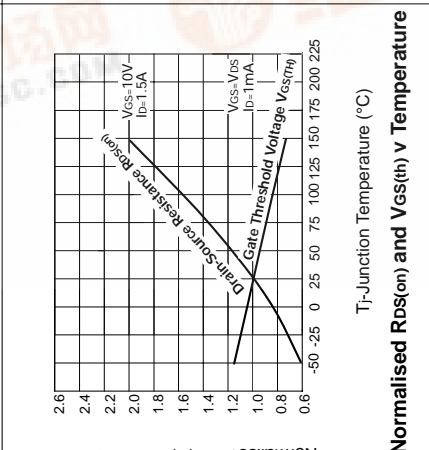
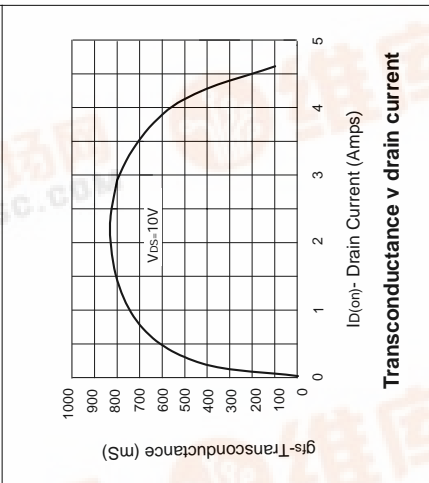
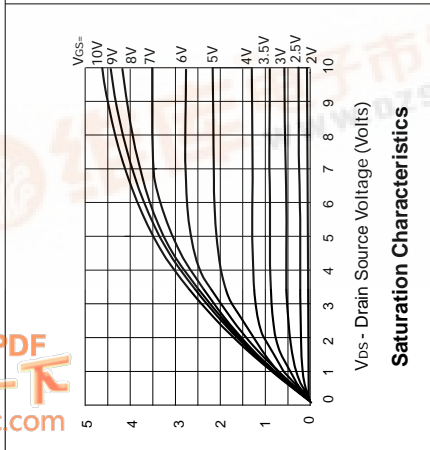
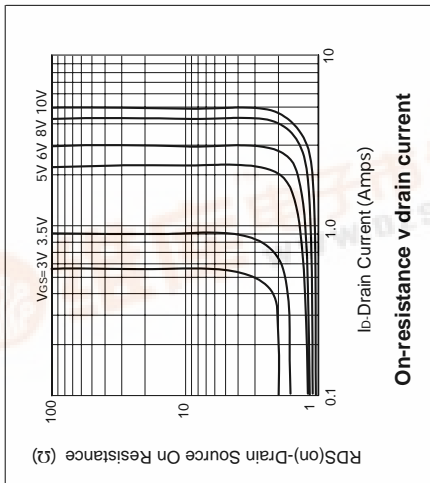




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TYPICAL CHARACTERISTICS

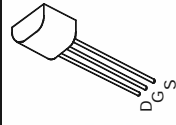


N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

FEATURES

- * 100 Volt V_{DS}
- * $R_{DS(on)} = 1.5\Omega$
- * Spice model available



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	100	V
Continuous Drain Current at $T_{amb}=25^\circ\text{C}$	I_D	450	mA
Pulsed Drain Current	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	700	mW
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D=1\text{mA}, V_{GS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D=1\text{mA}, V_{DS}=V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS}=\pm 20\text{V}, V_{DS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}		10 100	μA μA	$V_{DS}=100\text{V}, V_{GS}=0$ $V_{DS}=80\text{V}, V_{GS}=0\text{V}, T=125^\circ\text{C}(2)$
On-State Drain Current(1)	$I_{D(on)}$	2.5		A	$V_{DS}=25\text{V}, V_{GS}=10\text{V}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1.5 1.8	Ω	$V_{GS}=10\text{V}, I_D=1.5\text{A}$ $V_{GS}=5\text{V}, I_D=500\text{mA}$
Forward Transconductance(1)(2)gfs		250		mS	$V_{DS}=25\text{V}, I_D=1.5\text{A}$
Input Capacitance (2)	C_{iss}		100	pF	
Common Source Output Capacitance (2)	C_{oss}		40	pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$
Reverse Transfer Capacitance (2)	C_{riss}		12	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		4	ns	
Rise Time (2)(3)	t_r		8	ns	$V_{DD}=25\text{V}, I_D=1.5\text{A}$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		20	ns	
Fall Time (2)(3)	t_f		30	ns	

查询ZVN4210A供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

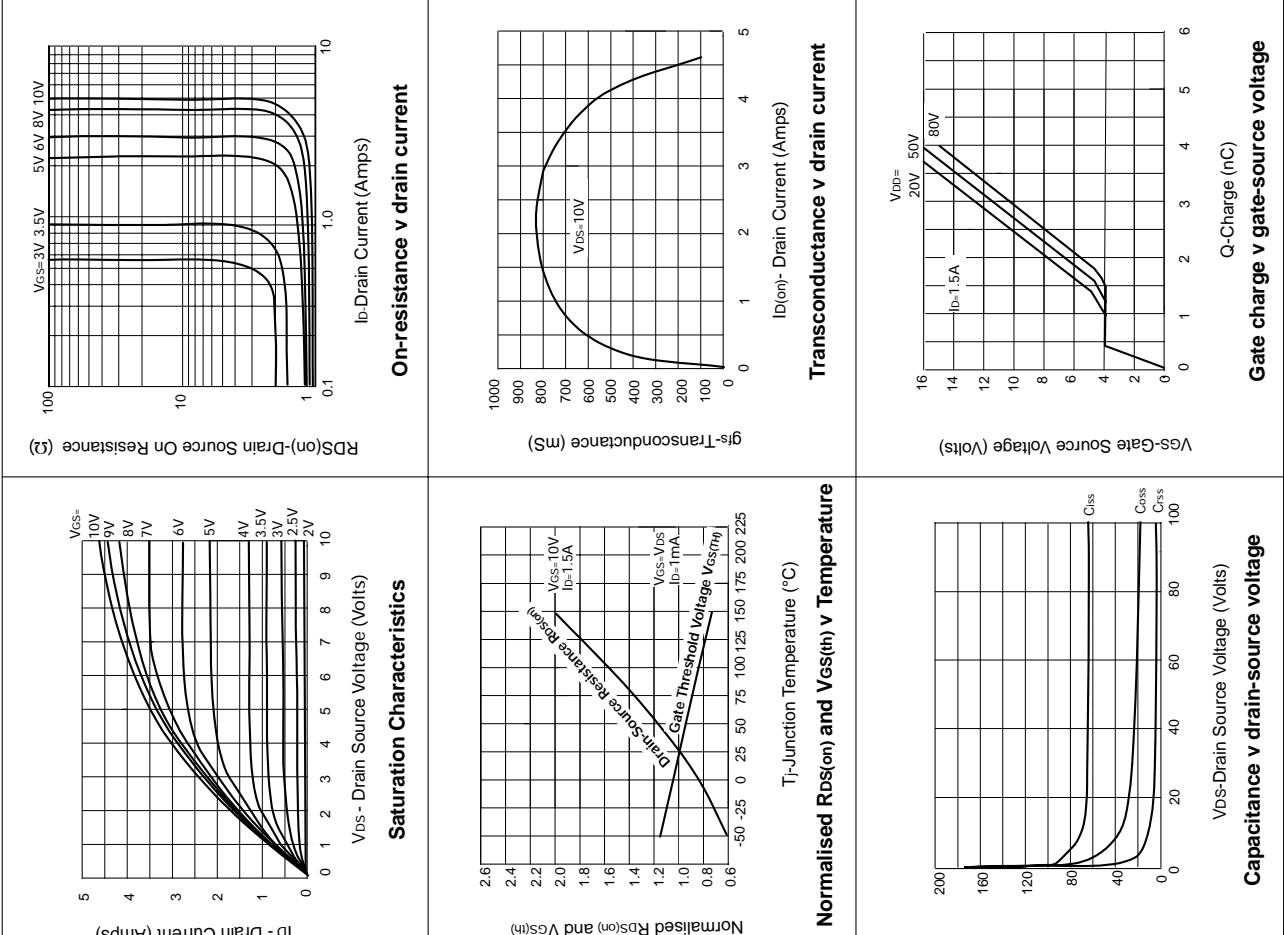
ISSUE 2 – MARCH 94

FEATURES

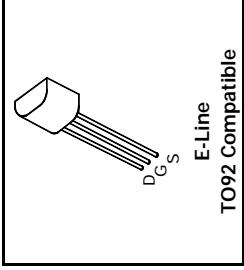
- * 100 Volt V_{DS}
- * $R_{DS(on)} = 1.5\Omega$
- * Spice model available

ZVN4210A

TYPICAL CHARACTERISTICS



ZVN4210A



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	V_{DS}	100	V
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Pulsed Drain Current	I_{DM}	6	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation at $T_{amb}=25^\circ C$	P_{tot}	700	mW
Operating and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	BV_{DSS}	100		V	$I_D = 1mA, V_{GS} = 0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	0.8	2.4	V	$I_D = 1mA, V_{DS} = V_{GS}$
Gate-Body Leakage	I_{GSS}		100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
Zero Gate Voltage Drain Current	I_{DSS}		10 100	μA μA	$V_{DS} = 100V, V_{GS} = 0$ $V_{DS} = 80V, V_{GS} = 0V, T = 125^\circ C(2)$
On-State Drain Current(1)	$I_{D(on)}$	2.5		A	$V_{DS} = 25V, V_{GS} = 10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		1.5 1.8	Ω	$V_{GS} = 10V, I_D = 1.5A$ $V_{GS} = 5V, I_D = 500mA$
Forward Transconductance(1)(2) g_{fs}		250		mS	$V_{DS} = 25V, I_D = 1.5A$
Input Capacitance (2)	C_{iss}		100	pF	
Common Source Output Capacitance (2)	C_{oss}		40	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$
Reverse Transfer Capacitance (2)	C_{riss}		12	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		4	ns	
Rise Time (2)(3)	t_r		8	ns	
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		20	ns	
Fall Time (2)(3)	t_f		30	ns	$V_{DD} = 25V, I_D = 1.5A$